



32V, 1.2MHz Rail-to-Rail Output CMOS Operational Amplifier

1 FEATURES

- Qualified for Automotive Applications
- AEC-Q100 Qualified with the Grade 1
- HIGH GAIN BANDWIDTH: 1.2MHz
- INPUT OFFSET VOLTAGE: ±0.5mV (Typical)
- QUIESCENT CURRENT: 120uA/Amp
- Rail to Rail Output
- Common-Mode Input Voltage Range
 Include Ground
- Supply Range: +3V to +32V
- SPECIFIED UP TO +125°C
- Micro SIZE PACKAGES: SOT23-5

2 APPLICATIONS

- SENSORS
- PHOTODIODE AMPLIFICATION
- ACTIVE FILTERS
- TEST EQUIPMENT
- DRIVING A/D CONVERTERS

3 DESCRIPTIONS

The RS841X-Q1 families of products offer high voltage (32V) operation and rail-to-rail output, as well as excellent speed/power consumption ratio, providing an excellent bandwidth (1.2MHz) and slew rate of 0.67V/us. The op-amps are unity gain stable and feature an ultra-low input bias current.

The devices are stable at capacitance up to 300pF.The input can operate normally within 100mV below of the negative power rail to 2V below of the positive power rail. The RS841X-Q1 families of operational amplifiers are specified at the full temperature range of -40°C to +125°C under single power supplies of 3V to 32V or dual power supplies of $\pm 1.5V$ to $\pm 16V$.

Device Information⁽¹⁾

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PART NUMBER	PACKAGE	BODY SIZE(NOM)					
RS8411-Q1	SOT23-5	2.92mm×1.62mm					
	SOP8	4.90mm×3.90mm					
RS8412-Q1	TSSOP8	3.00mm×4.40mm					
	MSOP8	3.00mm×3.00mm					

(1) For all available packages, see the orderable addendum at the end of the data sheet.



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4 Revision History Note: Page numbers for previous revisions may different from page numbers in the current version.

Version	Change Date	Change Item
A.1	2023/02/23	Initial version completed
A.2	2023/10/12	Add TSSOP8 Package
A.3	2024/01/24	1. Delete RS8414-Q1 Information 2. Update ELECTRICAL CHARACTERISTICS
A.3.1	2024/03/07	Modify packaging naming



5 PACKAGE/ORDERING INFORMATION⁽¹⁾

Orderable Device	Package Type	Pin	Channel	Lead finish/Ball material ⁽²⁾	MSL Peak Temp ⁽³⁾	Op Temp(°C)	Device Marking (4)	Package Qty
RS8411XF -Q1	SOT23-5	5	1	NIPDAUAG	MSL1-260°- Unlimited	-40°C ~125°C	8411	Tape and Reel,3000
RS8411BXF- Q1	SOT23-5	5	1	NIPDAUAG	MSL1-260°- Unlimited	-40°C ~125°C	8411B	Tape and Reel,3000
RS8412XK -Q1	SOP8	8	2	NIPDAUAG	MSL1-260°- Unlimited	-40°C ~125°C	RS8412	Tape and Reel,4000
RS8412XM -Q1	MSOP8	8	2	NIPDAUAG	MSL1-260°- Unlimited	-40°C ~125°C	RS8412	Tape and Reel,4000
RS8412XQ -Q1	TSSOP8	8	2	NIPDAUAG	MSL1-260°- Unlimited	-40°C ~125°C	RS8412	Tape and Reel,4000

NOTE:

(1) This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the right-hand navigation.

(2) Lead finish/Ball material. Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(3) MSL Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the lot trace code information (data code and vendor code), the logo or the environmental category on the device.



6 Pin Configuration and Functions (Top View)





Pin Description

NAME	I	-Q1 RS8411B-Q1 I/O ⁽¹⁾ DESCRIPTION		DESCRIPTION
INAME	RS8411-Q1			
+IN	3	1	I	Positive (noninverting) input
V-	2	2	-	Negative (lowest) power supply or ground (for single supply operation)
-IN	4	3	I	Negative (inverting) input
OUT	1	4	0	Output
V+	5	5	-	Positive (highest) power supply

(1) I = Input, O = Output.



Pin Configuration and Functions (Top View)



Pin Description

NAME	PIN SOP8/MSOP8 /TSSOP8	I/O ⁽¹⁾	DESCRIPTION
-INA	2	Ι	Inverting input, channel A
+INA	3	Ι	Noninverting input, channel A
-INB	6	Ι	Inverting input, channel B
+INB	5	Ι	Noninverting input, channel B
OUTA	1	0	Output, channel A
OUTB	7	0	Output, channel B
V-	4	-	Negative (lowest) power supply or ground (for single supply operation)
V+	8	-	Positive (highest) power supply

(1) I = Input, O = Output.



7 SPECIFICATIONS

7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT
	Supply, Vs=(V+) - (V-)		-0.7	36	
Voltage	Signal input pin ⁽²⁾		(V-)-0.2	(V+) +0.2	V
	Signal output pin ⁽³⁾		(V-)-0.2	(V+) +0.2	
	Signal input pin ⁽²⁾		-10	10	mA
Current	Signal output pin ⁽³⁾		-100	100	mA
	Output short-circuits (4)	Conti			
	Package thermal impedance ⁽⁵⁾	SOT23-5		230	°C/W
ALθ		SOP8		110	
ALO		MSOP8		170	
		TSSOP8		240	
	Operating range, T _A	-40	125		
Temperature	Junction, T _J ⁽⁶⁾	-40	150	°C	
	Storage, T _{stg}		-55	150	

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

- (2) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.2V beyond the supply rails should be current-limited to 10mA or less.
- (3) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.2V beyond the supply rails should be current-limited to ±100mA or less.

(4) Short-circuit to ground, one amplifier per package.

- (5) The package thermal impedance is calculated in accordance with JESD-51.
- (6) The maximum power dissipation is a function of $T_{J(MAX)}$, $R_{\theta JA}$, and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} T_A) / R_{\theta JA}$. All numbers apply for packages soldered directly onto a PCB.

7.2 ESD Ratings

The following ESD information is provided for handling of ESD-sensitive devices in an ESD protected area only.

			VALUE	UNIT
		Human-Body Model (HBM), per AEC Q100-002 ⁽¹⁾	±2000	V
V(ESD)	Electrostatic discharge	Charged-Device Model (CDM), per AEC Q100-011	±500	v
	Latch-Up (LU), per AEC Q100-004	±100	mA	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.



ESD SENSITIVITY CAUTION

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted).

		MIN	NOM	MAX	UNIT
	Single-supply	3		32	V
Supply voltage, Vs= (V+) - (V-)	Dual-supply	±1.5		±16	V
Operating range, T _A		-40		125	°C



7.4 ELECTRICAL CHARACTERISTICS

(At $T_A = +25^{\circ}$ C, $V_S=3V$ to 32V, $R_L = 10k\Omega$ connected to $V_S/2$, and $V_{OUT} = V_S/2$, Full ⁽⁹⁾ = -40°C to +125°C, unless otherwise noted.) ⁽¹⁾

	DADAMETED	CONDITIONS	т	RS841X-Q1			UNIT	
		CONDITIONS	T,	MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT	
POWER	SUPPLY						•	
Vs	Operating Voltage Range		25°C	3		32	V	
		Vs=±2.5V, Io=0mA	25°C		120	280		
la	Quiescent Current Per	Vs=±2.5V, 10=0MA	Full			350	μA	
Iq Amplifier	Amplifier	Vs=±16V, Io=0mA	25°C		175	340		
		V3-±10V, 10-011A	Full			470		
PSRR	Power-Supply Rejection Ratio	Vs=5V to 32V	25°C	95	120		dB	
FJKK		VS-5V t0 52V	Full	90			uв	
INPUT		1						
Vos	Input Offset Voltage	V _{CM} = V _S /2	25°C	-2	±0.5	2	mV	
V 03			Full	-3		3	v	
Vos Tc	Input Offset Voltage Average Drift ⁽⁴⁾		Full		±3		μV/°C	
IB	Input Bias Current ^{(4) (5)}	V _{CM} = V _S /2	25°C		±10		pА	
los	Input Offset Current ⁽⁴⁾	V _{CM} = V _S /2	25°C		±10		pА	
Vсм	Common-Mode Voltage Range	Vs= ±16V	Full	(V-)-0.1		(V+)-2	V	
CNADD	Common-Mode Rejection	V _S = ±16V	25°C	100	110		JD	
CMRR Ratio		V _{CM} =(V-)+0.5V to (V+)-2V	Full	90			dB	
OUTPU	г							
Δ	Open-Loop Voltage Gain	R _L =10KΩ, Vo=(V-)+0.6V to (V+)-0.6V	25°C	83	115		dB	
A _{OL}	Open-Loop voltage Gain		Full	53				
Vон			25°C	15.8			- v	
VOH	Output Swing	Vs=±16V, RL=10KΩ	Full	15.7				
V _{OL}	Output Swing	$V_{S}=\pm 10V, R_{L}=10R_{S2}$	25°C			-15.8	V	
VOL			Full			-15.7	v	
lsc	Short-Circuit Current ^{(6) (7)}		25°C	±35	±80		mA	
ISC	Short-Circuit Current (A)		Full	±15			IIIA	
CLOAD	Capacitive Load Drive		25°C		100		pF	
FREQUE	ENCY RESPONSE							
SR	Slew Rate ⁽⁸⁾	G=+1, CL=100pF	25°C		0.67		V/µs	
GBW	Gain-Bandwidth Product		25°C		1.2		MHz	
ts	Settling Time,0.01%	V _s =±2.5V, G=+1, C _L =100pF, Step=2V	25°C		5		μs	
t _{OR}	Overload Recovery Time	V _{IN} •Gain≥V _S , G=11	25°C		5		μs	
ton	Turn On Time		25°C		10		μs	
NOISE		•			•			
En	Input Voltage Noise	f = 0.1Hz to 10Hz, Vs=±2.5V	25°C		16		μVpp	
en	Input Voltage Noise Density ⁽⁴⁾	f = 1KHz	25°C		45		nV/√Hz	





NOTE:

- (1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device.
- (2) Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical quality control (SQC) method.
- (3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration.
- (4) This parameter is ensured by design and/or characterization and is not tested in production.
- (5) Positive current corresponds to current flowing into the device.
- (6) The maximum power dissipation is a function of $T_{J(MAX)}$, $R_{\theta JA}$, and T_A . The maximum allowable power dissipation at any ambient temperature is PD = ($T_{J(MAX)} T_A$) / $R_{\theta JA}$. All numbers apply for packages soldered directly onto a PCB.
- (7) Short circuit test is a momentary test.
- (8) Number specified is the slower of positive and negative slew rates.
- (9) Specified by characterization only.



7.5 TYPICAL CHARACTERISTICS

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At $T_A = +25^{\circ}$ C, Vs=±16V, R_L = 10k Ω connected to V_S/2, V_{OUT} = V_S/2, unless otherwise noted.











Figure 5. SMALL SIGNAL STEP RESPONSE



Figure 2. SUPPLY VOLTAGE vs QUIESCENT CURRENT



Figure 4. LARGE SIGNAL STEP RESPONSE



Figure 6. SMALL SIGNAL STEP RESPONSE



TYPICAL CHARACTERISTICS

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At $T_A = +25^{\circ}$ C, Vs=±16V, R_L = 10k Ω connected to Vs/2, V_{OUT} = Vs/2, unless otherwise noted.







Figure 9. Output Voltage Swing vs Output Current



Figure 8. NEGATIVE OVERVOLTAGE RECOVERY



Figure 10. 0.1Hz to 10Hz NOISE AT Vs=5V



8 Detailed Description

8.1 Overview

The RS841X-Q1 operational amplifier provides high overall performance, making these devices designed for many general-purpose applications. The excellent offset drift of only 3μ V/°C provides excellent stability over the entire temperature range. In addition, the device offers very good overall performance with high CMRR, PSRR, and A_{OL}.

8.2 Operating Characteristics

The RS841X-Q1 amplifier is specified for operation from 3 V to 32 V (\pm 1.5 V to \pm 16 V). Many of the specifications apply from -40°C to +125°C.

8.3 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but can involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits for protection from accidental ESD events both before and during product assembly.

A good understanding of this basic ESD circuitry and the relevance to an electrical overstress event is helpful. Figure 11 shows the ESD circuits contained in the RS841X-Q1. The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where the diodes meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.



Figure 11. ESD block diagram

An ESD event produces a short-duration, high-voltage pulse that is transformed into a short-duration, high current pulse when discharging through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent damage. The energy absorbed by the protection circuitry is then dissipated as heat.

When an ESD voltage develops across two or more amplifier device pins, current flows through one or more steering diodes. Depending on the path that the current takes, the absorption device can activate. The absorption device has a trigger, or threshold voltage, that is above the normal operating voltage of the RS841X-Q1 but below the device breakdown voltage level. When this threshold is exceeded, the absorption device quickly activates and clamps the voltage across the supply rails to a safe level.

When the operational amplifier connects into a circuit, as shown in Figure 11, the ESD protection components are intended to remain inactive and do not become involved in the application circuit operation. However, circumstances can arise where an applied voltage exceeds the operating voltage range of a given pin. If this condition occurs, there is a risk that some internal ESD protection circuits can turn on and conduct current. Any such current flow occurs through steering-diode paths and rarely involves the absorption device.



Much of what happens in the circuit depends on the supply characteristics. If V+ can sink the current, then one of the upper input steering diodes conducts and directs current to V+. Excessively high current levels can flow with increasingly higher V_{IN} . As a result, the data sheet specifications recommend that applications limit the input current to 10 mA.

If the supply is not capable of sinking the current, V_{IN} can begin sourcing current to the operational amplifier and then take over as the source of positive supply voltage. The danger in this case is that the voltage can rise to levels that exceed the operational amplifier absolute maximum ratings.

Another common question involves what happens to the amplifier if an input signal is applied to the input when the power supplies (V+ or V-) are at 0 V. Again, this question depends on the supply characteristic when at 0 V, or at a level below the input signal amplitude. If the supplies appear as high impedance, then the input source supplies the operational amplifier current through the current-steering diodes. This state is not a normal bias condition; most likely, the amplifier does not operate normally. If the supplies are low impedance, then the current through the steering diodes can become quite high. The current level depends on the ability of the input source to deliver current and any resistance in the input path.

The input pins of the RS841X-Q1 are protected from excessive differential voltage with back-to-back diodes; see Figure 11. In most circuit applications, the input protection circuitry has no effect. However, in low-gain or G = 1 circuits, fast-ramping input signals can forward-bias these diodes because the output of the amplifier cannot respond rapidly enough to the input ramp. If the input signal is fast enough to create this forward-bias condition, then limit the input signal current to 10 mA or less. If the input signal current is not inherently limited, an input series resistor can limit the input signal current. This input series resistor degrades the low-noise performance of the RS841X-Q1. Figure 11 shows an example configuration that implements a current-limiting feedback resistor.



9 Application and Implementation

Information in the following applications sections is not part of the RUNIC component specification, and RUNIC does not warrant its accuracy or completeness. RUNIC's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 APPLICATION NOTE

The RS841X-Q1 operational amplifier provides high overall performance in a large number of general-purpose applications. As with all amplifiers, applications with noisy or high-impedance power supplies require decoupling capacitors placed close to the device pins. In most cases, 0.1μ F capacitors are adequate. Follow the additional recommendations in the Layout Guidelines section to achieve the maximum performance from this device. Many applications introduce capacitive loading to the output of the amplifier (which potentially causes instability). To stabilize the amplifier, add an isolation resistor between the amplifier output and the capacitive load.

9.2 Typical Applications

This circuit can drive capacitive loads (such as cable shields, reference buffers, MOSFET gates, and diodes). The circuit uses an isolation resistor (R_{ISO}) to stabilize the output of an operational amplifier. R_{ISO} modifies the open-loop gain of the system to ensure that the circuit has sufficient phase margin.



Figure 12. Unity-Gain Buffer with $R_{\rm ISO}$ Stability Compensation

9.3 Design Requirements

The design requirements are:

- Supply voltage: 30 V (±15 V)
- \bullet Capacitive loads: 100 pF, 1000 pF, 0.01 μ F, 0.1 μ F, and 1 μ F
- Phase margin: 45° and 60°

9.4 Detailed Design Procedure

Figure 12 shows a unity-gain buffer driving a capacitive load. Equation 1 shows the transfer function for the circuit in Figure 12. Figure 12 does not show the open-loop output resistance of the operational amplifier (R_0).

$$T(s) = \frac{1}{1 + (R_0 + R_{ISO}) \times C_{LOAD} \times S}$$

(1)

The transfer function in Equation 1 has a pole and a zero. The frequency of the pole (f_p) is determined by ($R_0 + R_{ISO}$) and C_{LOAD} . The R_{ISO} and C_{LOAD} components determine the frequency of the zero (f_z). A stable system is obtained by selecting R_{ISO} so that the rate of closure (ROC) between the open-loop gain (A_{OL}) and $1/\beta$ is 20 dB per decade.



10 Layout

10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the
operational amplifier itself. Bypass capacitors are used to reduce the coupled noise by providing low
impedance power sources local to the analog circuitry.

-Connect low-ESR, 0.1μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single supply applications.

- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current.
- In order to reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in Figure 14, keeping R_F and R_G close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

10.2 Layout Example



Figure 13. Schematic Representation





NOTE: Layout Recommendations have been shown for dual op-amp only, follow similar precautions for Single and four.



11 PACKAGE OUTLINE DIMENSIONS SOT23-5⁽³⁾





RECOMMENDED LAND PATTERN (Unit: mm)





Symphol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Мах	
A ⁽¹⁾		1.250		0.049	
A1	0.000	0.150	0.000	0.006	
A2	1.000	1.200	0.039	0.047	
b	0.360	0.500	0.014	0.020	
с	0.100	0.200	0.004	0.008	
D ⁽¹⁾	2.826	3.026	0.111	0.119	
E ⁽¹⁾	1.526	1.726	0.060	0.068	
E1	2.600	3.000	0.102	0.118	
e	0.950(0.950(BSC) ⁽²⁾		BSC) ⁽²⁾	
e1	1.800	2.000	0.071	0.079	
L	0.350	0.600	0.014	0.024	
θ	0°	8°	0°	8°	

NOTE:

1. Plastic or metal protrusions of 0.15mm maximum per side are not included.

2. BSC (Basic Spacing between Centers), "Basic" spacing is nominal.

3. This drawing is subject to change without notice.



MSOP8⁽³⁾





RECOMMENDED LAND PATTERN (Unit: mm)





Symphol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min	Min Max		Max	
A ⁽¹⁾	0.820	1.100	0.032	0.043	
A1	0.020	0.150	0.001	0.006	
A2	0.750	0.950	0.030	0.037	
b	0.250	0.380	0.010	0.015	
С	0.090	0.230	0.004	0.009	
D ⁽¹⁾	2.900	3.100	0.114	0.122	
е	0.650(BSC) ⁽²⁾	0.026(BSC) ⁽²⁾	
E ⁽¹⁾	2.900	3.100	0.114	0.122	
E1	4.750	5.050	0.187	0.199	
L	0.400	0.800	0.016	0.031	
θ	0°	6°	0°	6°	

NOTE:

Plastic or metal protrusions of 0.15mm maximum per side are not included.
 BSC (Basic Spacing between Centers), "Basic" spacing is nominal.

3. This drawing is subject to change without notice.



TSSOP8⁽³⁾





RECOMMENDED LAND PATTERN (Unit: mm)





Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
A ⁽¹⁾		1.200		0.047		
A1	0.050	0.150	0.002	0.006		
A2	0.900	1.050	0.035	0.041		
b	0.200	0.280	0.008	0.011		
с	0.130	0.170	0.005	0.007		
D ⁽¹⁾	2.900	3.100	0.114	0.122		
E ⁽¹⁾	4.300	4.500	0.169	0.177		
E1	6.200	6.600	0.244	0.260		
e	0.650(BSC) ⁽²⁾		0.026(BSC) ⁽²⁾			
L	0.450	0.750	0.018	0.030		
Н	0.250)(TYP)	0.010(TYP)			
θ	0°	8°	0°	8°		

NOTE:

1. Plastic or metal protrusions of 0.15mm maximum per side are not included.

2. BSC (Basic Spacing between Centers), "Basic" spacing is nominal.
 3. This drawing is subject to change without notice.



SOP8⁽²⁾











RECOMMENDED LAND PATTERN (Unit: mm)

Detail	Х

Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Мах	Min	Max		
A ⁽¹⁾		1.750		0.069		
A ₁	0.100	0.250	0.004	0.010		
A ₂	1.250	1.450	0.049	0.057		
A ₃	0.2	250	0.010			
bp	0.360	0.490	0.014	0.019		
с	0.190	0.250	0.007	0.010		
D ⁽¹⁾	4.800	5.000	0.190	0.200		
E ⁽¹⁾	3.800	4.000	0.150	0.160		
HE	5.800	6.200	0.228	0.244		
е	1.2	270	0.050			
L	1.050		0.041			
Lp	0.400	1.000	0.016	0.039		
Q	0.600	0.700	0.024	0.028		
Z	0.300	0.700	0.012	0.028		
у	0.1	100	0.004			
θ	0°	8°	0°	8°		

NOTE:

1. Plastic or metal protrusions of 0.15mm maximum per side are not included.

2. This drawing is subject to change without notice.





12 TAPE AND REEL INFORMATION REEL DIMENSIONS

TAPE DIMENSION



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

	Reel	Reel Width	A0	BO	К0	P0	P1	P2	W	Pin1
Package Type	Diameter	W1(mm)	(mm)	во (mm)	(mm)	(mm)	(mm)	(mm)	vv (mm)	Quadrant
SOT23-5	7"	9.5	3.20	3.20	1.40	4.0	4.0	2.0	8.0	Q3
SOP8	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1
MSOP8	13"	12.4	5.20	3.30	1.50	4.0	8.0	2.0	12.0	Q1
TSSOP8	13"	12.4	6.90	3.45	1.65	4.0	8.0	2.0	12.0	Q1

NOTE:

1. All dimensions are nominal.

2. Plastic or metal protrusions of 0.15mm maximum per side are not included.



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